

ZXTP25020BFH

20V, SOT23, PNP medium power transistor

Summary

$BV_{CEX} > -40V$

$BV_{CEO} > -20V$

$BV_{ECO} > -7V$

$I_{C(cont)} = -4A$

$R_{CE(sat)} = 32\text{ m}\Omega$

$V_{CE(sat)} < -60mV @ 1A$

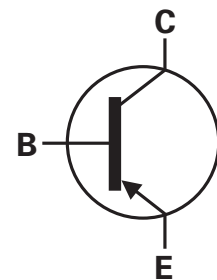
$P_D = 1.25W$

Complementary part number ZXTN25020BFH



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

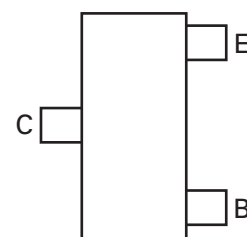


Features

- High power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 40V forward blocking voltage
- 7V reverse blocking voltage

Applications

- MOSFET and IGBT gate driving
- DC - DC converters
- Motor drive
- High side driver
- Battery charging



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25020BFHTA	7	8	3,000

Device marking

1A9

ZXTP25020BFH

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	-40	V
Collector-emitter voltage (forward blocking)	V_{CEX}	-40	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-collector voltage (reverse blocking)	V_{ECO}	-7	V
Emitter-base voltage	V_{EBO}	-7	V
Continuous collector current ^(b)	I_C	-4	A
Peak pulse current	I_{CM}	-10	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$	P_D	0.73	W
Linear derating factor		5.84	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$	P_D	1.05	W
Linear derating factor		8.4	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(c)}$	P_D	1.25	W
Linear derating factor		9.6	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$	P_D	1.81	W
Linear derating factor		14.5	mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	°C

Thermal resistance

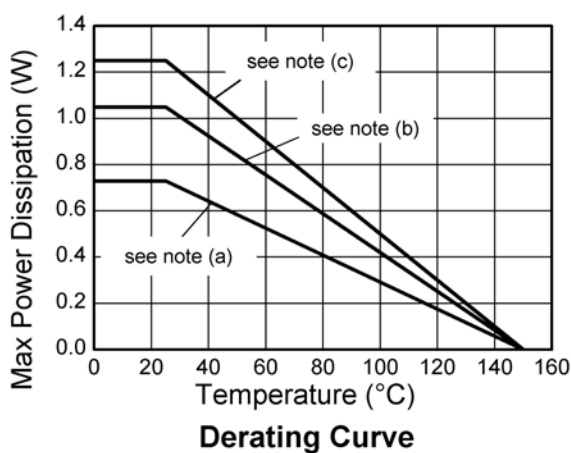
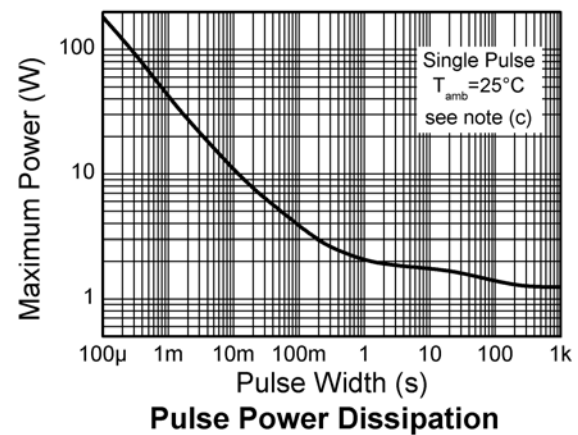
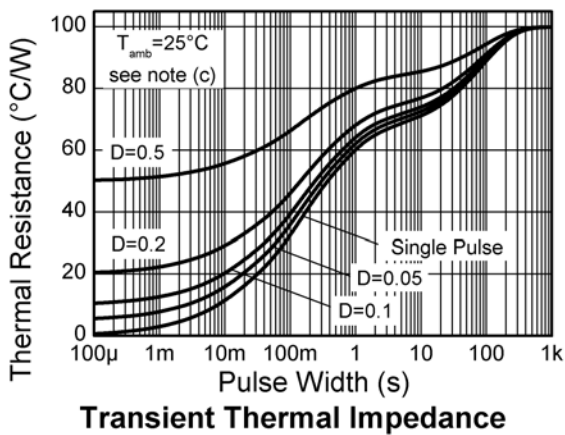
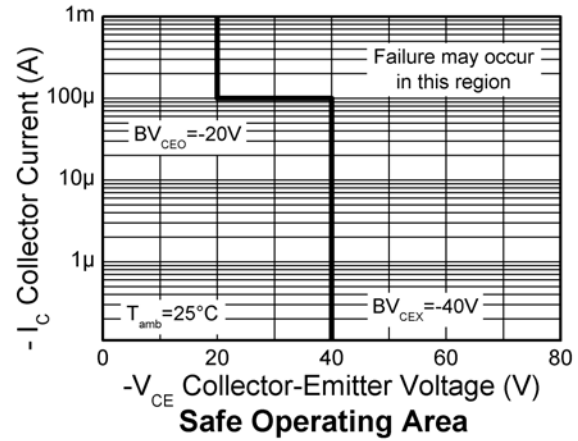
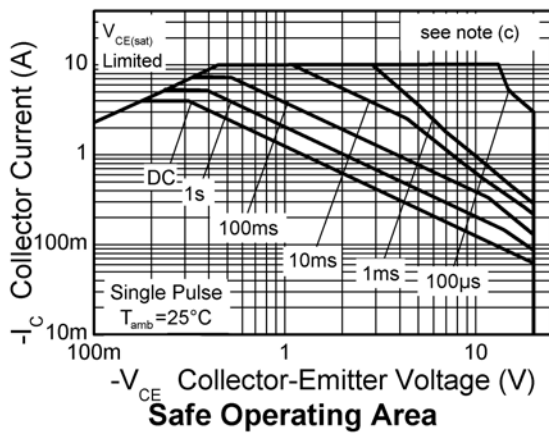
Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	171	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	119	°C/W
Junction to ambient ^(c)	$R_{\theta JA}$	100	°C/W
Junction to ambient ^(d)	$R_{\theta JA}$	69	°C/W

NOTES:

- (a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (d) As (c) above measured at $t < 5$ secs.

ZXTP25020BFH

Characteristics



ZXTP25020BFH

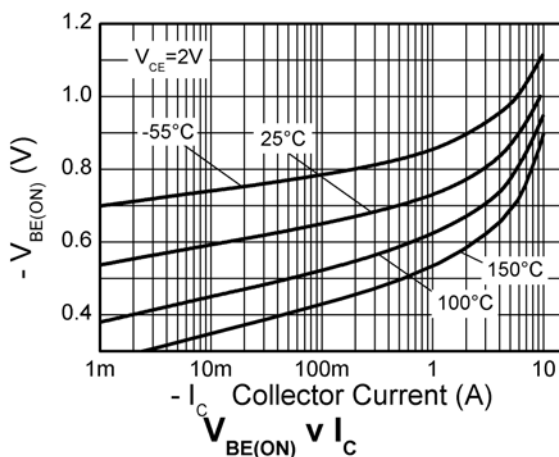
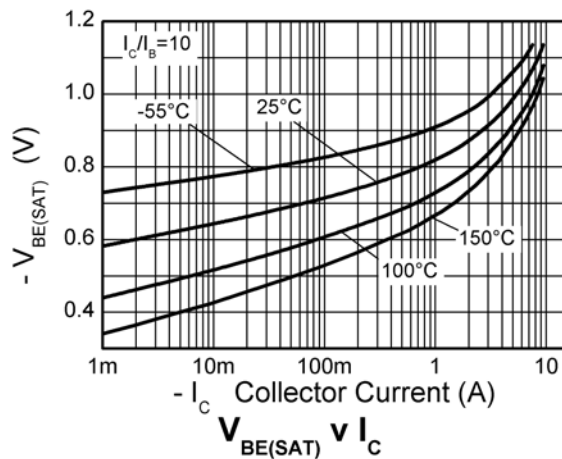
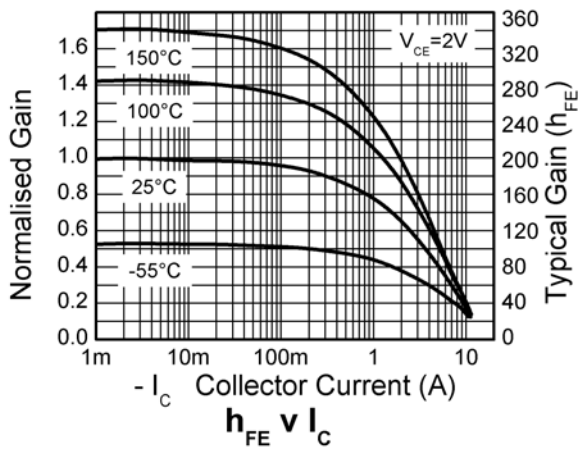
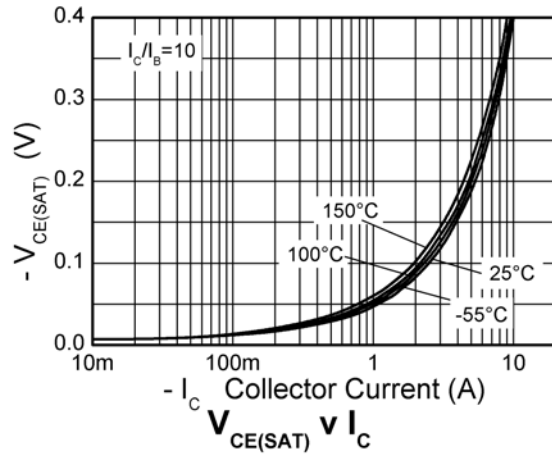
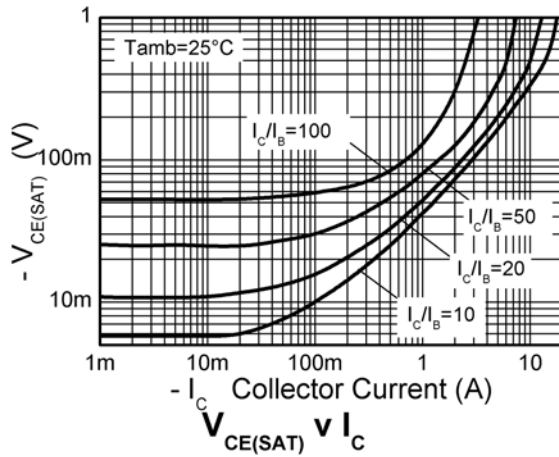
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-40	-60		V	$I_C = -100\mu\text{A}$
Collector-emitter breakdown voltage (forward blocking)	BV_{CEX}	-40	-60		V	$I_E = -100\mu\text{A}^{(*)}$ $R_{BE} < 1\text{k}\Omega$ or $1\text{V} < V_{BE} < -0.25\text{V}$
Collector-emitter breakdown voltage (base open)	BV_{CEO}	-20	-35		V	$I_C = -10\text{mA}^{(*)}$
Emitter-base breakdown voltage	BV_{EBO}	-7	-8.2		V	$I_E = -100\mu\text{A}$
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	-6	-8		V	$I_E = -100\mu\text{A}^{(*)}$ $R_{BC} < 10\text{k}\Omega$ or $0.25 < V_{BC} < -0.25\text{V}$
Emitter-collector breakdown voltage (base open)	BV_{ECO}	-7	-8.6		V	$I_E = -100\mu\text{A}^{(*)}$
Collector-base cut-off current	I_{CBO}		<-1	-50 -20	nA μA	$V_{CB} = -32\text{V}$ $V_{CB} = -32\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Collector-emitter cut-off current	I_{CEX}		-	100	nA	$V_{CE} = -32\text{V}$; $R_{BE} < 1\text{k}\Omega$ or $1\text{V} < V_{BE} < -0.25\text{V}$
Emitter-base cut-off current	I_{EBO}		<-1	-50	nA	$V_{EB} = -5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		-44 -80 -125 -160 -160	-60 -110 -190 -210 -210	mV mV mV mV mV	$I_C = -1\text{A}$, $I_B = -100\text{mA}^{(*)}$ $I_C = -1\text{A}$, $I_B = -20\text{mA}^{(*)}$ $I_C = -2\text{A}$, $I_B = -40\text{mA}^{(*)}$ $I_C = -4\text{A}$, $I_B = -200\text{mA}^{(*)}$ $I_C = -5\text{A}$, $I_B = -500\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		-930	-1000	mV	$I_C = -4\text{A}$, $I_B = -200\text{mA}^{(*)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		-820	-900	mV	$I_C = -4\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
Static forward current transfer ratio	h_{FE}	100 80 50	200 160 100	300		$I_C = -10\text{mA}$, $V_{CE} = -2\text{V}^{(*)}$ $I_C = -1\text{A}$, $V_{CE} = -2\text{V}^{(*)}$ $I_C = -4\text{A}$, $V_{CE} = -2\text{V}^{(*)}$ $I_C = -10\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
Transition frequency	f_T		250		MHz	$I_C = -50\text{mA}$, $V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output capacitance	C_{OBO}		32.5	40	pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}^{(*)}$
Delay time	t_d		53		ns	$V_{CC} = -15\text{V}$,
Rise time	t_r		63		ns	$I_C = -750\text{mA}$,
Storage time	t_s		128		ns	$I_{B1} = I_{B2} = -15\text{mA}$
Fall time	t_f		50		ns	

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



ZXTP25020BFH

Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
c	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
e	0.95 NOM		0.037 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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